AW312B Datasheet

Zhuhai Jieli Technology Co.,LTD

Version V1.0

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Revision History

Date	Revision	Description
2024.12.24	V1.0	Initial Release





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AW312B Features

SYSTEM

- > 32bit CPU 160MHz
- Support MATH/AES128
- I-cache
- Support EMU
- On-chip SRAM 32kbyte
- Support MPU
- Support UDMA
- ➢ Built-In Flash
- ➤ 24MHz crystal oscillator
- > Internal low jitter low power RC oscillator
- Internal PLL

Bluetooth

- BLE6.0 +2.4GHz-Proprietary (DN Q334307)
- Support AoA Transmitter
- Support long range BLE
- Maximum transmitting power 9dBm
- Receiver sensitivity
 - ◆ -97dBm @BLE-1Mbps
 - ◆ -95dBm @BLE-2Mbps

Peripherals

- 1 x Full speed USB
- 4 x Multi-function 32bit timer
- ➤ 1 x IR RX/TX
- 3 x UART interface
- 1 x I²C Master/Slave interface
- 2 x SPI Master/Slave interface
- ➤ 1 x QDEC
- ➤ 4 x MCPWM
- ➤ 2 x LEDC
- > 1 x 10bit ADC(10 Channels)
- 9 x GPIO Support function remapping

PMU

- Support temperature sensor
- ➤ VPWR range 2.7V to 5.5V
- ➤ IOVDD range 1.8V to 3.6V
- > Deep sleep mode (IOVDD @3.0V)
 - 170nA (External wakeup)
 - 1.37uA (32kHz RC OSC+wakeup)
 - 2.9uA (32kHz RC OSC+wakeup+16k retention SRAM)

Packages

➤ SOP16

Temperature

- Operating temperature
 - TC = -20° C to $+85^{\circ}$ C (standard range)
 - $TC = -40^{\circ}C$ to $+105^{\circ}C$ (extended range)
- Storage temperature -65°C to +150°C

Applications

- Mouse devices
- Non-audio remote controller
- Selfie stick
- Page turner
- Adaptive USB
- Bluetooth moudle
- Price tag and other diversified IOT product



1 Block Diagram

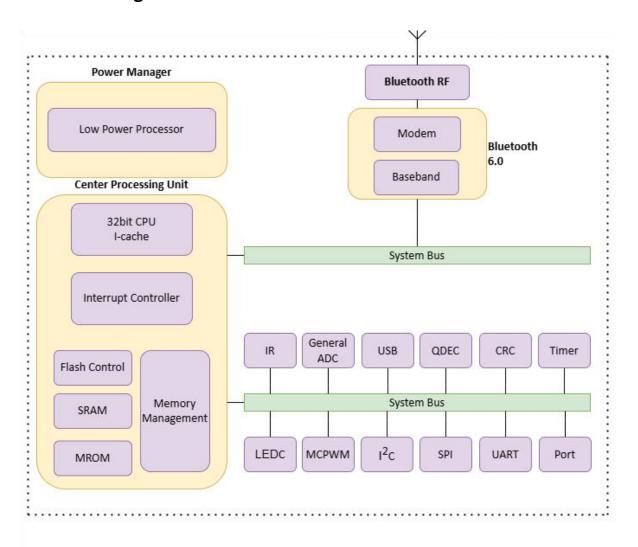


Figure 1-1 AW312B Block Diagram



2 Pin Definition

2.1 Pin Assignment

USBDM USBDP PA11 PA10 IOVDD VPWR/PA7 PA9 PA8	1 2 3 4 5 6 7 8	AW312B SOP16	16 15 14 13 12 11 10 9	XOSCO XOSCI VSS BTRF PA1 PA2 PA3 PA4
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Figure 2-1 AW312B Pin Assignment



2.2 Pin Description

Table 2-2-1 AW312B Pin Description

Pin No.	Name	Туре	IO Initial State	Description
1	USBDM	1/0	15kΩ Pull-down	ADC13(ADC Input Channel 13)
2	USBDP	1/0	15kΩ Pull-down	ADC14(ADC Input Channel 14)
3	PA11	1/0	10kΩ Pull-up	ADC11(ADC Input Channel 11) Hold down 0 to reset
4	PA10	1/0	Z	ADC10(ADC Input Channel 10)
5	IOVDD	Р		IO Power
	VPWR	Р		Battery Input
6	PA7	1/0	Z	- X
7	PA9	1/0	Z	LVD(External Low Voltage Detection Input) ADC9(ADC Input Channel 9) SPIO_DAT3B
8	PA8	I/O	z	ADC8(ADC Input Channel 8) SPI0_DAT2B
9	PA4	1/0	10kΩ Pull-up	ADC4(ADC Input Channel 4) MCLR(Device Reset)
10	PA3	1/0	z	ADC3(ADC Input Channel 3) SPIO_DIB(1)
11	PA2	1/0	Z	ADC2(ADC Input Channel 2) SPIO_DOB(0)
12	PA1	1/0	Z	ADC1(ADC Input Channel 1) SPIO_CLKB
13	BTRF	RF	-	Bluetooth RF Antenna
14	VSS	G	+	Ground
15	XOSCI	1	-	Crystal Oscillator Input
16	xosco	0		Crystal Oscillator Output

Note

1.IO initial state abbreviations Z--High resistance, H--High level, L--Low level, X--May be changed during power on.

2.Timer, IR,MCPWM, QDEC, UART, LEDC, I²C, SPI1 functions can be remapped to any I/O.

Table 2-2-2 Pin Types Description

Pin Type	Description	Pin Type	Description
Р	Power	1/0	Input or Output
G	Ground	Į	Input
RF	RF antenna	0	Output

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3 Electrical Characteristics

3.1 Absolute Maximum Ratings

Table 3-1 Absolute Maximum Ratings

Symbol	Parameter	Min	Max	Unit
Topt	Operating temperature	-20	+85	${\mathbb C}$
Tstg	Storage temperature	-65	+150	$^{\circ}$
VPWR	Constant Vallege	-0.3	6.0	V
IOVDD	Supply Voltage	-0.3	3.6	V
GPIO	Input voltage of GPIO (except PA7)	-0.3	3.6	V
HVTIO	Input voltage of HVT-IO (PA7)	-0.3	6.0	V

Note

3.2 ESD Ratings

Table 3-2 ESD Ratings

Parameter	Тур	Test pin	Reference standard
Human Body Mode	±8kV	All pins	JEDEC EIA/JESD22-A114
Machine Mode	±400V	All pins	JEDEC EIA/JESD22-A115
Charge Device Model	±2kV	All pins	ANSI/ESDA/JEDEC JS-002-2022

3.3 PMU Characteristics

Table 3-3-1 PMU Characteristics under VPWR supply

	Table 5 2 1 me characteristics and a 1 m supply							
Symbol	Parameter	Conditions	Min	Тур	Max	Unit		
VPWR	Power supply	-	2.7		5.5	V		
Operating mo	Operating mode							
Symbol	Parameter	Conditions	Min	Тур	Max	Unit		
	Voltage output			3.0		V		
IOVDD	Loading current	IOVDD=3.0V@VPWR = 3.7V			60	mA		
Low Power m	ode							
Symbol	Parameter	Conditions	Min	Тур	Max	Unit		
IOVDD	Loading current	IOVDD=3.0V@VPWR = 3.7V			8	mA		

Table 3-3-2 PMU Characteristics under IOVDD supply

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
IOVDD	Power supply	-	1.8		3.6	V

^{1.}Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device.



3.4 IO Characteristics

Table 3-4 IO Characteristics

Input Char	acteristics						
Symbol	Parameter	Conditions	10	Min	Max	Unit	
W	Lave Lavel Incret Valtage	10//00 3 0//	PA1~PA4	0.2	1.4		
V_{IL}	Low-Level Input Voltage	IOVDD = 3.0V	PA7~PA11	-0.3	1.4	V	
			PA1~PA4				
		IOVDD = 3.0V	PA8~PA11	4 7	2.2	V	
V_{IH}	High-Level Input Voltage	10000 = 3.00	USBDP	1.7	3.3	V	
			USBDM				
		IOVDD = 3.0V	PA7	1.7	5.5	V	
Output Ch	aracteristics						
Symbol	Parameter	Conditions	10	T	ур	Unit	
I _{OL}	Output Current	IOVDD = 3.0V Voutput = 0.3V	PA1~PA4 PA8~PA11	9(HI 21(H	D=0) D=1) ID=2) ID=3)	mA	
		IOVDD = 3.0V Voutput = 0.3V	PA7 USBDP USBDM	8		mA	
Іон	Output Current	IOVDD = 3.0V Voutput = 2.7V	PA1~PA4 PA8~PA11	3(HD=0) 9(HD=1) 21(HD=2) 54(HD=3)		mA	
		IOVDD = 3.0V Voutput = 2.7V	PA7 USBDP USBDM			mA	
	esistance Characteristics						
Symbol	Parameter	Conditions	10		ур	Unit	
			PA1~PA4		PU=1)		
		IOVDD = 3.0V	PA7~PA11	1	PU=2)	Ω	
R_{pu}	Pull-up Resistance			1M(PU=3)			
		IOVDD = 3.0V	USBDP		5k	Ω	
		IOVDD = 3.0V	USBDM		80k	Ω	
			PA1~PA4		PD=1)		
		IOVDD = 3.0V	PA7~PA11	1	PD=2)	Ω	
R_{pd}	Pull-down Resistance			1M(F	PD=3)		
		IOVDD = 3.0V	USBDP	1	15k		
			USBDM			Ω	

Note

1.Internal pull-up/pull-down resistance accuracy ±20%.



3.5 BT Characteristics

3.5.1 Transmitter

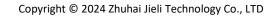
Table 3-5-1 Transmitter characteristics

Parameter	Conditions	Min	Тур	Max	Unit
Maximum RF Transmit Power	BLE-1Mbps		8	9	dBm

3.5.2 Receiver

Table 3-5-2 Receiver characteristics

Parameter	Conditions	Min	Тур	Max	Unit
Sensitivity	BLE-1Mbps		-97		dBm
	BLE-2Mbps	/	-95		dBm
	BLE-S2		-100		dBm
	BLE-S8		-105	//	dBm





4 Package Information

4.1 SOP16

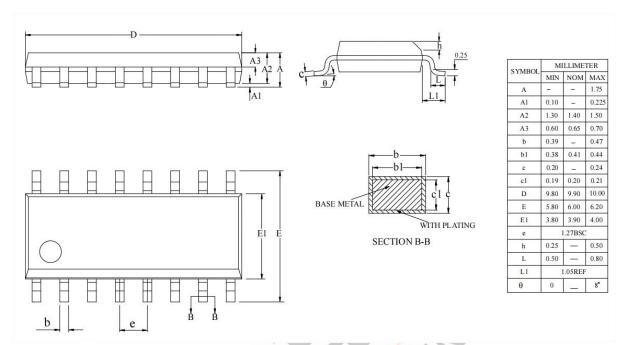


Figure 4-1 AW312B Package



5 IC Marking Information

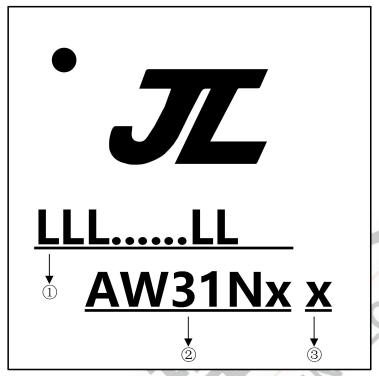


Figure 5-1 AW312B Package Outline

- 1 LLL.....LL LOT No. , It contains 7 to 18 alphanumerics
- 2 AW31Nx Chip Model
- (3) x Built-in flash size
 - 0 No Flash Memory
 - 2 2Mbit Flash
 - 4 4Mbit Flash



6 Solder-Reflow Condition

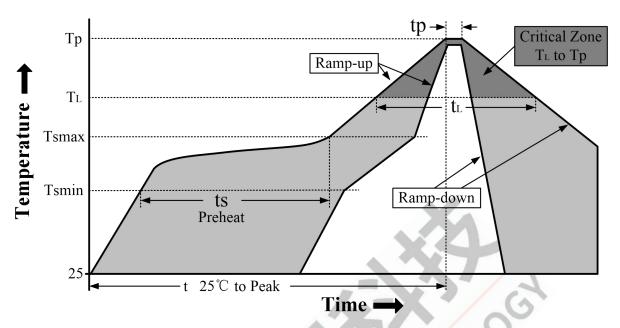


Figure 6-1 Classification Reflow Profile

Table 6-1 Classification Profiles

Profile Feature		Sn-Pb Eutectic Assembly	Pb-Free Assembly
	Temperature Min (T _{smin})	100℃	150℃
Preheat/Soak	Temperature Max (T _{smax})	150°C	200℃
	Time (ts) from (T _{smin} to T _{smax})	60-120 seconds	60-180 seconds
Average ramp-up rate (T _{smax} to T _p)		3℃/second max	3℃/second max
Liquidus temperature (T _L)		183℃	217℃
Time (t _L) maintained <mark>above T_L</mark>		60-150 seconds	60-150 seconds
Peak package body temperature (T _p)		See Table 6-2	See Table 6-3
Time within 5℃ of actual		10-30 seconds	20-40 seconds
Peak Temperature (tp) ²			
Ramp-down rate (Tp to TL)		6°C/second max	6℃/second max
Time 25℃ to peak temperature		6 minutes max	8 minutes max

Note

- 1.All temperatures refer to topside of the package, measured on the package body surface
- 2.Time within 5 $^{\circ}$ C of actual peak temperature (tp) specified for the reflow profiles is a "supplier" and "user" maximum.

Table 6-2 SnPb Classification Temperature

Package	Volume mm³	Volume mm³ ≥ 350	
Thickness	< 350		
<2.5 mm	240 +0/-5℃	225 +0/-5°C	
≥2.5 mm	225 +0/-5℃	225 +0/-5℃	



Table 6-3 Pb-free - Classification Temperature

Package	Volume mm³	Volume mm³	Volume mm³
Thickness	< 350	350 - 2000	> 2000
< 1.6mm	260℃	260℃	260℃
1.6 mm - 2.5mm	260℃	250℃	245℃
> 2.5mm	250 ℃	245℃	245℃

Note

1.*Tolerance The device manufacturer/supplier shall assure process compatibility up to and including the stated classification temperature (this means Peak reflow temperature +0 $^{\circ}$ C.For example 260 $^{\circ}$ C+0 $^{\circ}$ C)at the rated MSL level.

